

Ordering number : ENA1270A



RD2004LN

Diffused Junction Silicon Diode

Ultrahigh-Speed Switching Diode

Features

- High breakdown voltage (VRRM=400V).
- High reliability.
- One-point fixing type plastic molded package facilitating easy mounting and heat dissipation.
- Fast reverse recovery time.
- Low noise at the time of reverse recovery.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		400	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		400	V
Average Output Current	IO		20	A
Surge Forward Current	IFSM	Sine wave, 10ms single pulse	180	A
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	VR	IR=1mA	400			V
Forward Voltage	VF	IF=20A		1.3	1.5	V
Reverse Current	IR	VR=400V			100	μA
Reverse Recovery Time	trr1	IF=10A, di / dt=100A/μS		44	50	ns
	trr2	IF=0.5A, IR=1A		20		ns
Thermal Resistance	Rth(j-c)	Junction-Case : Smoothed DC			4.0	°C / W

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Package Dimensions

unit : mm (typ)

7509-004

